

TOSHIBA

2SA1940

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

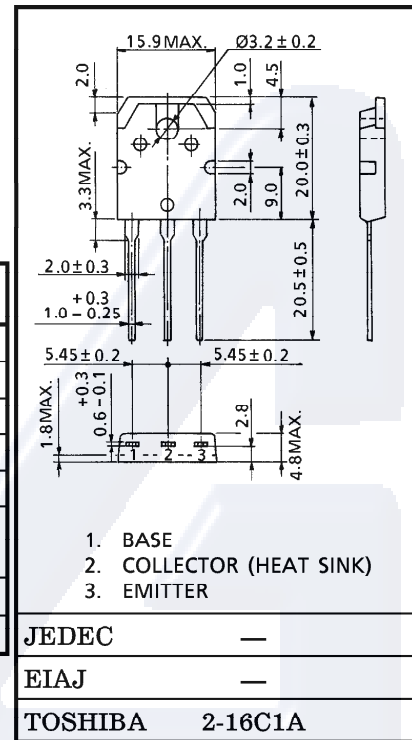
2SA1940

POWER AMPLIFIER APPLICATIONS

- Complementary to 2SC5197
- Recommend for 55W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	-120	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-8	A
Base Current	I_B	-0.8	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)	P_C	80	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 4.7g (Typ.)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -120V, I_E = 0$	—	—	-5.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-5.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C = -50mA, I_B = 0$	-120	—	—	V
DC Current Gain	$h_{FE} (1)$ (Note)	$V_{CE} = -5V, I_C = -1A$	55	—	160	
	$h_{FE} (2)$	$V_{CE} = -5V, I_C = -4A$	35	75	—	
Collector-Emitter Saturation Voltage	$V_{CE (sat)}$	$I_C = -6A, I_B = -0.6A$	—	-0.80	-2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5V, I_C = -4A$	—	-0.97	-1.5	V
Transition Frequency	f_T	$V_{CE} = -5V, I_C = -1A$	—	30	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	260	—	pF

Note : $h_{FE(1)}$ Classification R : 55~110, O : 80~160

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